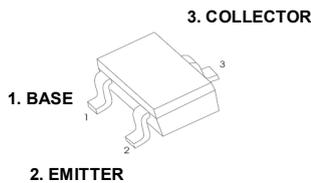
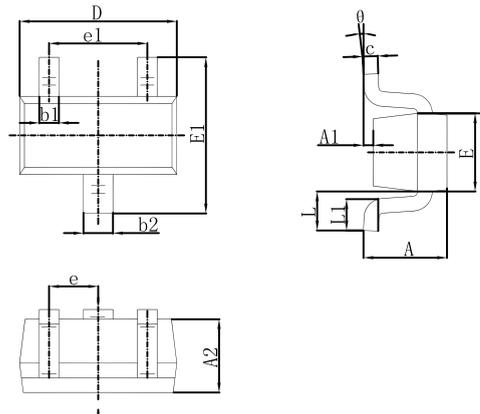


### FEATURES

- Complementary to MMBT3906T
- Small Package



### SOT-523



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Dimensions in inches and (millimeters)

### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{\text{CBO}}$	Collector-Base Voltage	60	V
$V_{\text{CEO}}$	Collector-Emitter Voltage	40	V
$V_{\text{EBO}}$	Emitter-Base Voltage	6	V
$I_{\text{C}}$	Collector Current	200	mA
$P_{\text{C}}$	Collector Power Dissipation	150	mW
$R_{\theta\text{JA}}$	Thermal Resistance From Junction To Ambient	833	$^{\circ}\text{C}/\text{W}$
$T_{\text{j}}$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{\text{stg}}$	Storage Temperature	-55~+150	$^{\circ}\text{C}$

# MMBT3904T

## ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =10μA, I <sub>E</sub> =0	60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	40			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> =30V, V <sub>EB(off)</sub> =3V			50	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			100	nA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =1mA	70			
	h <sub>FE(2)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =10mA	100		300	
	h <sub>FE(3)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =50mA	60			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			0.2	V
		I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.3	V
Collector-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA	0.65		0.85	V
		I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.95	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =20V, I <sub>C</sub> =10mA, f=100MHz	300			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =5V, I <sub>E</sub> =0, f=1MHz			4	pF
Base input capacitance	C <sub>ib</sub>	V <sub>EB</sub> =0.5V, I <sub>C</sub> =0, f=1MHz			8	pF
Delay time	t <sub>d</sub>	V <sub>CC</sub> =3V, V <sub>BE(off)</sub> =-0.5V I <sub>C</sub> =10mA, I <sub>B1</sub> =1mA			35	ns
Rise time	t <sub>r</sub>	V <sub>CC</sub> =3V, V <sub>BE(off)</sub> =-0.5V I <sub>C</sub> =10mA, I <sub>B1</sub> =1mA			35	ns
Storage time	t <sub>s</sub>	V <sub>CC</sub> =3V, I <sub>C</sub> =10mA, I <sub>B1</sub> = I <sub>B2</sub> =1mA			200	ns
Fall time	t <sub>f</sub>	V <sub>CC</sub> =3V, I <sub>C</sub> =10mA, I <sub>B1</sub> = I <sub>B2</sub> =1mA			50	ns

## RATING AND CHARACTERISTIC CURVES ( MMBT3904T )

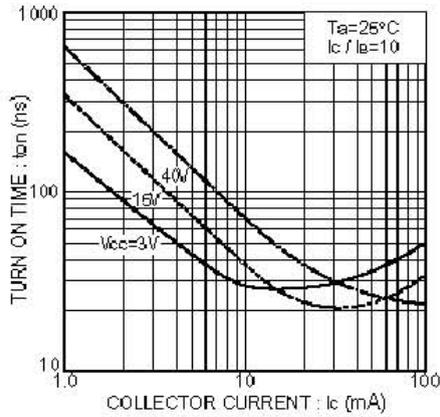


Fig. 5 Turn-on time vs. collector current

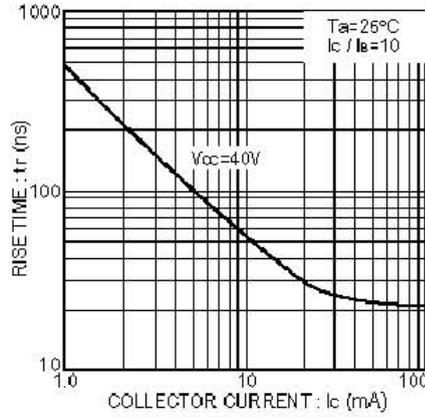


Fig. 6 Rise time vs. collector current

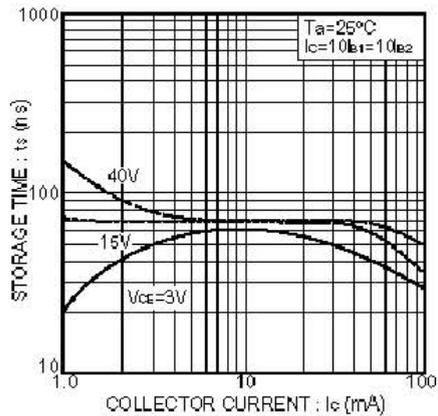


Fig. 7 Storage time vs. collector current

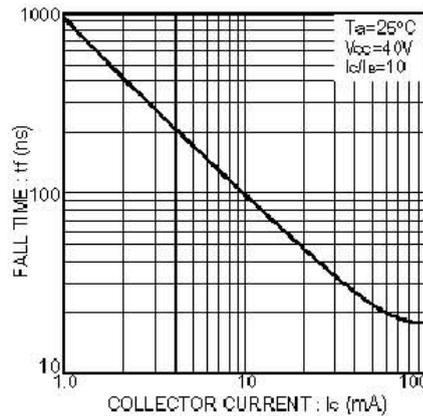


Fig. 8 Fall time vs. collector current

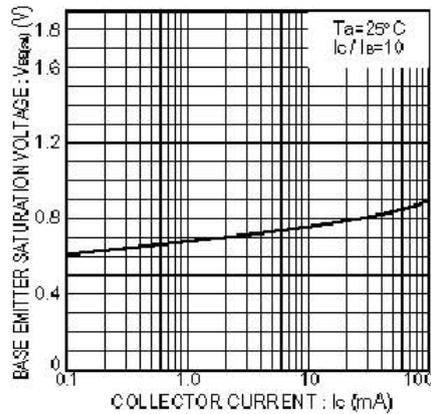


Fig. 9 Base-emitter saturation voltage vs. collector current

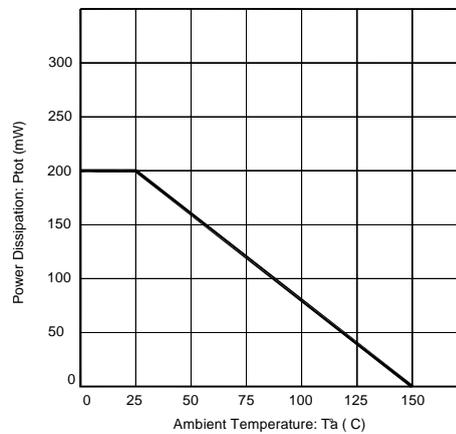


Fig. 10 Power Dissipation vs Ambient Temperature